IN THE CLAIMS:

Please amend the claims as follows:

1. (**Currently Amended**) A dielectric device comprising:

such a first electrode layer that constituent elements located on its surface are terminated by halogen atoms; and

a dielectric film formed on the surface of said first electrode layer terminated by said halogen atoms,

wherein said first electrode layer contains at least one element selected from a group consisting of Pt, Ir, Pd and Ru and said halogen atoms are fluorine atoms.

Claims 2-3. (**Cancelled**)

4. (**Currently Amended**) The dielectric device according to claim 1 ~~3~~, wherein said first electrode layer contains Pt, and platinum fluoride is formed on the surface of said first electrode layer.

5. (**Original**) The dielectric device according to claim 1, wherein said dielectric film includes a ferroelectric film having a bismuth layer structure.

6. (**Original**) The dielectric device according to claim 5, wherein said ferroelectric film having a bismuth layer structure is an $SrBi_2Ta_2O_9$ (SBT) film.

7. (**Original**) The dielectric device according to claim 5, wherein a bismuth layer is formed to be substantially perpendicular to said first electrode layer in said ferroelectric film having a bismuth layer structure.

8. (**Original**) The dielectric device according to claim 1, further comprising a second electrode layer formed on said dielectric film.

9. (**Original**) The dielectric device according to claim 1, further comprising an adherent layer formed under said first electrode layer.

10. (**Original**) The dielectric device according to claim 9, wherein said adherent layer includes an IrSiN film.

11. (**Withdrawn**) A method of manufacturing a dielectric device comprising steps of:

terminating constituent elements located on the surface of a first electrode layer by halogen atoms; and

forming a dielectric film on the surface of said first electrode layer terminated by said halogen atoms.

12. (**Withdrawn**) The method of manufacturing a dielectric device according to claim 11, wherein said step of terminating said constituent elements by said halogen atoms includes a step of exposing the surface of said first electrode layer into either a plasma or a solution containing halogen ions thereby terminating said constituent elements located on the surface of said first electrode layer by said halogen atoms.

13. (**Withdrawn**) The method of manufacturing a dielectric device according to claim 11, further comprising a step of performing heat treatment after formation of said dielectric film thereby crystallizing said dielectric film.

14. (**Withdrawn**) The method of manufacturing a dielectric device according to claim 11, wherein said halogen atoms are fluorine atoms.

15. (**Withdrawn**) The method of manufacturing a dielectric device according to claim 14, wherein said first electrode layer contains Pt, and platinum fluoride is formed on the surface of said first electrode layer.

16. (**Withdrawn**) The method of manufacturing a dielectric device according to claim 11, wherein said step of forming said dielectric film includes a step of forming a ferroelectric film having a bismuth layer structure.

17. (**Withdrawn**) The method of manufacturing a dielectric device according to claim 16, wherein said ferroelectric film having a bismuth layer structure is an $SrBi_2Ta_2O_9$ (SBT) film.

18. (**Withdrawn**) The method of manufacturing a dielectric device according to claim 16, wherein said step of forming said ferroelectric film having a bismuth layer structure includes a step of forming said ferroelectric film having a bismuth layer structure so that a bismuth layer is substantially perpendicular to said first electrode layer.

19. (**Withdrawn**) The method of manufacturing a dielectric device according to claim 11, further comprising a step of forming a second electrode layer on said dielectric film.

20. (**Withdrawn**) The method of manufacturing a dielectric device according to claim 11, further comprising a step of forming an adherent layer under said first electrode layer.

21. (**Withdrawn**) The method of manufacturing a dielectric device according to claim 20, wherein

said adherent layer includes an IrSiN film.